

ABSTRACT:

An electro-optical device such as a fingerprint sensor or an X-ray image sensor has an ITO (indium tin oxide) layer (67) and a SiN layer (64A) near the ITO layer. An intermediate layer (64B) of silicon oxide is provided between the ITO layer and the SiN layer. This intermediate layer prevents reduction of the ITO layer during manufacture.

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Fig. 6

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